047N08NS3-VB Datasheet

N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) [a]	Q_g (Typ.)
80	0.0048 at V_{GS} = 10 V	60	25 nC
	0.0050 at V_{GS} = 7.5 V	60	
	0.0064 at V_{GS} = 4.5 V	60	

FEATURES

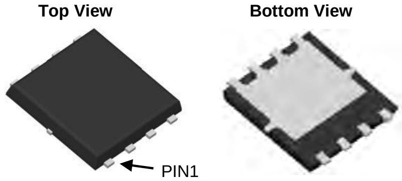
- Trench power MOSFET
- 100 % R_g and UIS tested

RoHS COMPLIANT
HALOGEN FREE

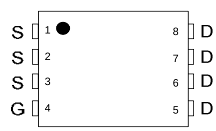
APPLICATIONS

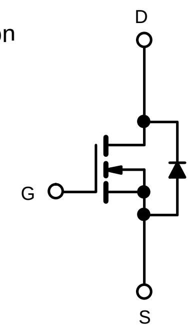
- Primary side switching
- Synchronous rectification
- DC/AC inverters

DFN5X6



Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	60 [a]	A
	T_C = 70 °C		60 [a]	
	T_A = 25 °C		23.8 [b, c]	
	T_A = 70 °C		19 [b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	100	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	60 [a]	
	T_A = 25 °C		5.6 [b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	35	
Single Pulse Avalanche Energy		E_{AS}	61	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	104	W
	T_C = 70 °C		66.6	
	T_A = 25 °C		6.25 [b, c]	
	T_A = 70 °C		4 [b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C
Soldering Recommendations (Peak Temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient [b, f]	t ≤ 10 s	R_{thJA}	15	20	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	0.9	1.2	

Notes

a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. The DFN 5X6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 54 °C/W.

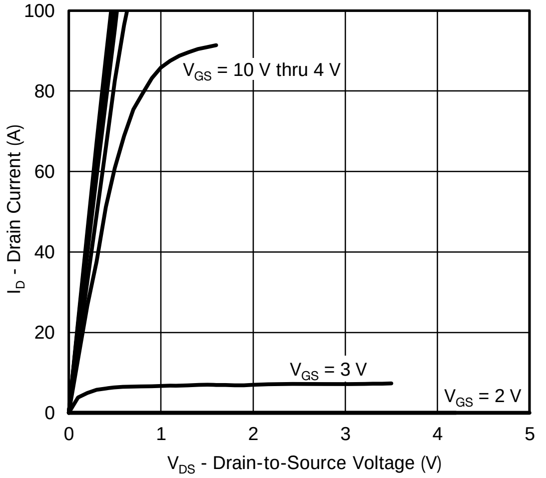
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	80	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	-	47	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-5.7	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.2	-	2.8	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55 °C	-	-	10	
On-State Drain Current [a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A	-	0.0048	-	Ω
		V_{GS} = 7.5 V, I_D = 20 A	-	0.0050	-	
		V_{GS} = 4.5 V, I_D = 15 A	-	0.0064	-	
Forward Transconductance [a]	g_{fs}	V_{DS} = 10 V, I_D = 20 A	-	68	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz	-	2800	-	pF
Output Capacitance	C_{oss}		-	1100	-	
Reverse Transfer Capacitance	C_{rss}		-	93	-	
Total Gate Charge	Q_g	V_{DS} = 40 V, V_{GS} = 10 V, I_D = 20 A	-	57	86	nC
		V_{DS} = 40 V, V_{GS} = 7.5 V, I_D = 20 A	-	42	63	
		V_{DS} = 40 V, V_{GS} = 4.5 V, I_D = 20 A	-	25	38	
Gate-Source Charge	Q_{gs}		-	8.5	-	
Gate-Drain Charge	Q_{gd}		-	10	-	
Output Charge	Q_{oss}	V_{DS} = 40 V, V_{GS} = 0 V	-	70	105	
Gate Resistance	R_g	f = 1 MHz	0.3	0.95	1.9	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 2 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω	-	9	18	ns
Rise Time	t_r		-	12	24	
Turn-Off Delay Time	$t_{d(off)}$		-	34	68	
Fall Time	t_f		-	7	14	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 40 V, R_L = 2 Ω $I_D \cong$ 20 A, V_{GEN} = 7.5 V, R_g = 1 Ω	-	16	32	
Rise Time	t_r		-	15	30	
Turn-Off Delay Time	$t_{d(off)}$		-	32	64	
Fall Time	t_f		-	8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	60	A
Pulse Diode Forward Current [a]	I_{SM}		-	-	100	
Body Diode Voltage	V_{SD}	I_S = 5 A	-	0.73	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, dI/dt = 100 A/µs, T_J = 25 °C	-	53	105	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	65	130	nC
Reverse Recovery Fall Time	t_a		-	25	-	ns
Reverse Recovery Rise Time	t_b		-	28	-	

Notes

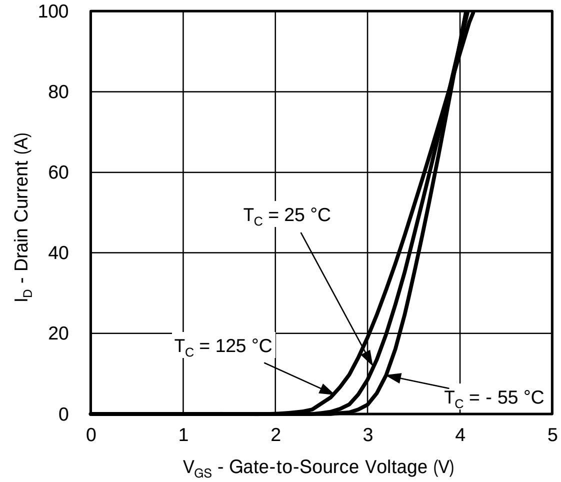
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

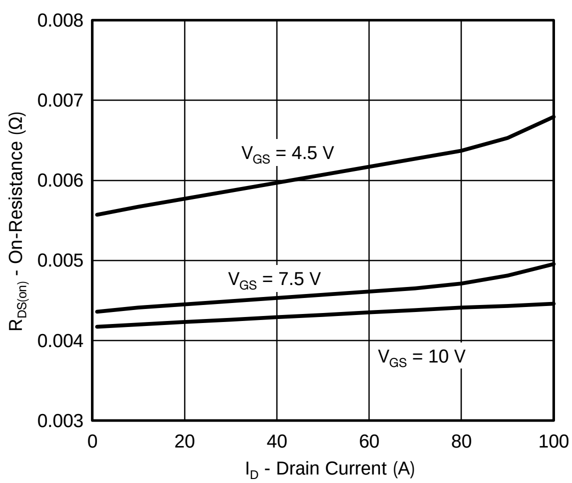
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



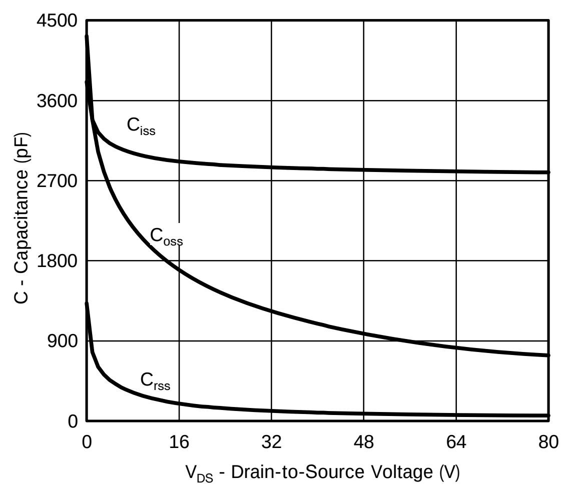
Output Characteristics



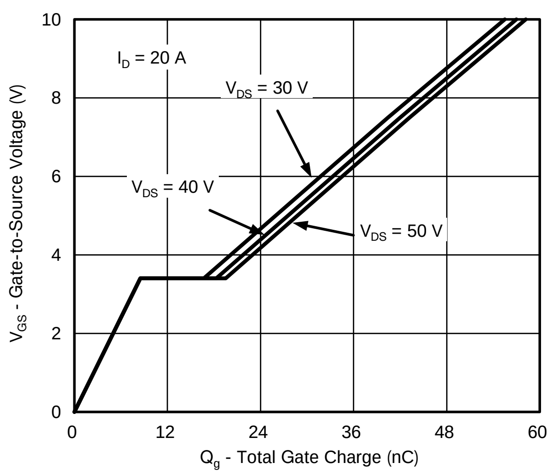
Transfer Characteristics



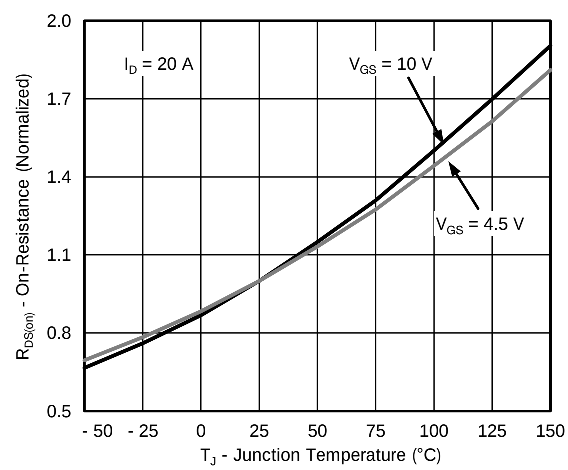
On-Resistance vs. Drain Current



Capacitance

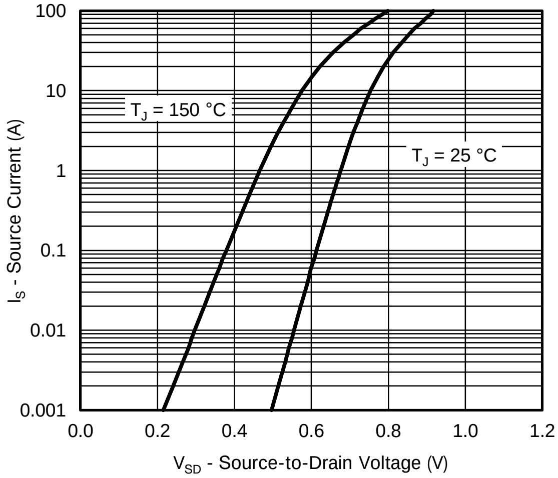


Gate Charge

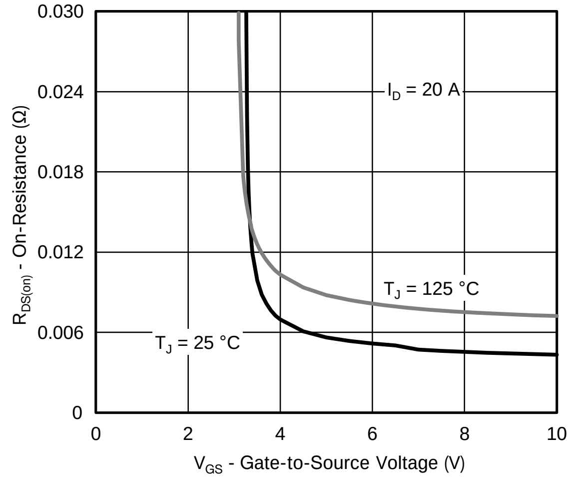


On-Resistance vs. Junction Temperature

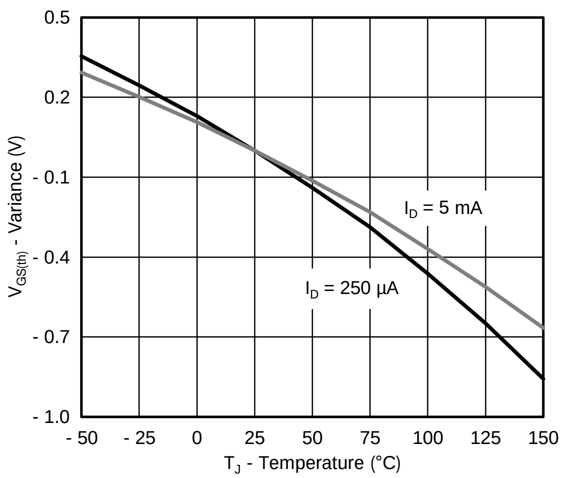
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



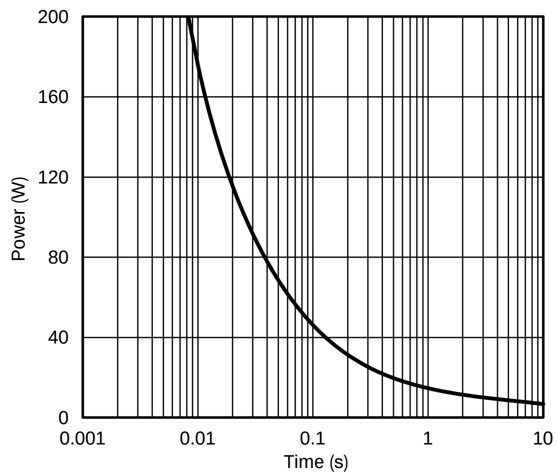
Source-Drain Diode Forward Voltage



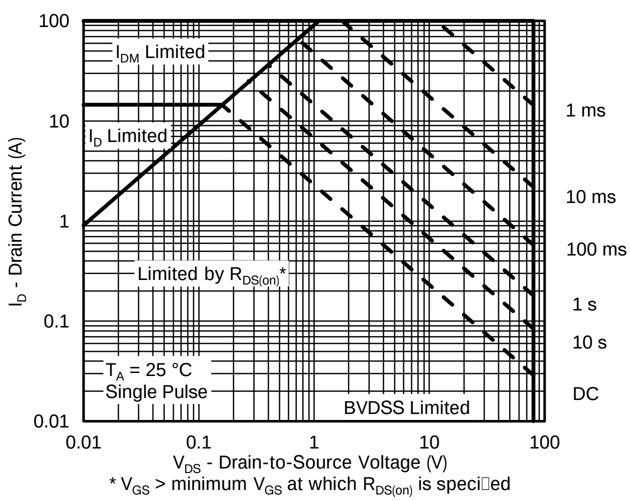
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

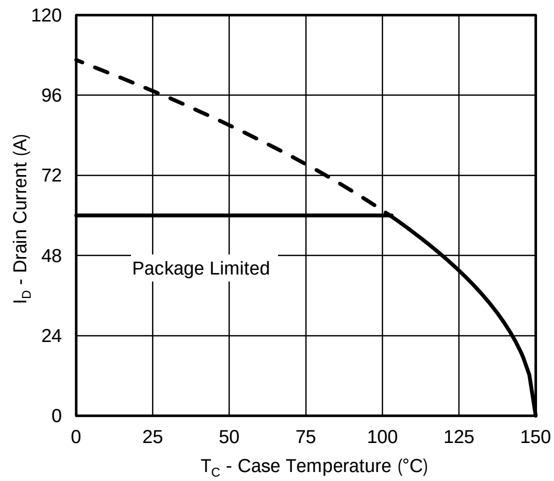


Single Pulse Power, Junction-to-Ambient

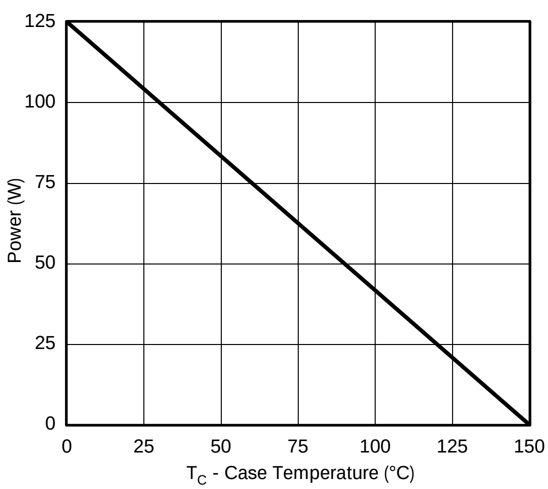


Safe Operating Area, Junction-to-Ambient

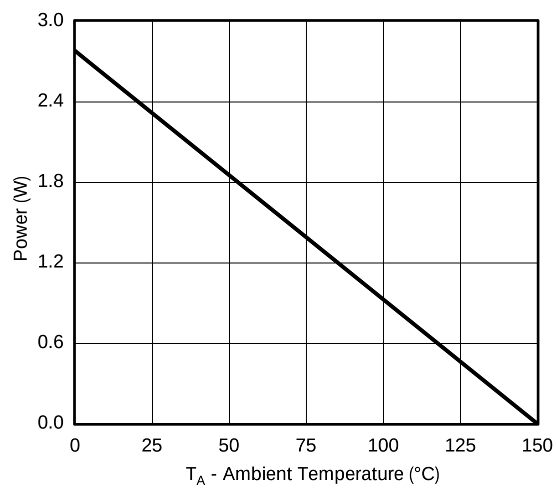
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



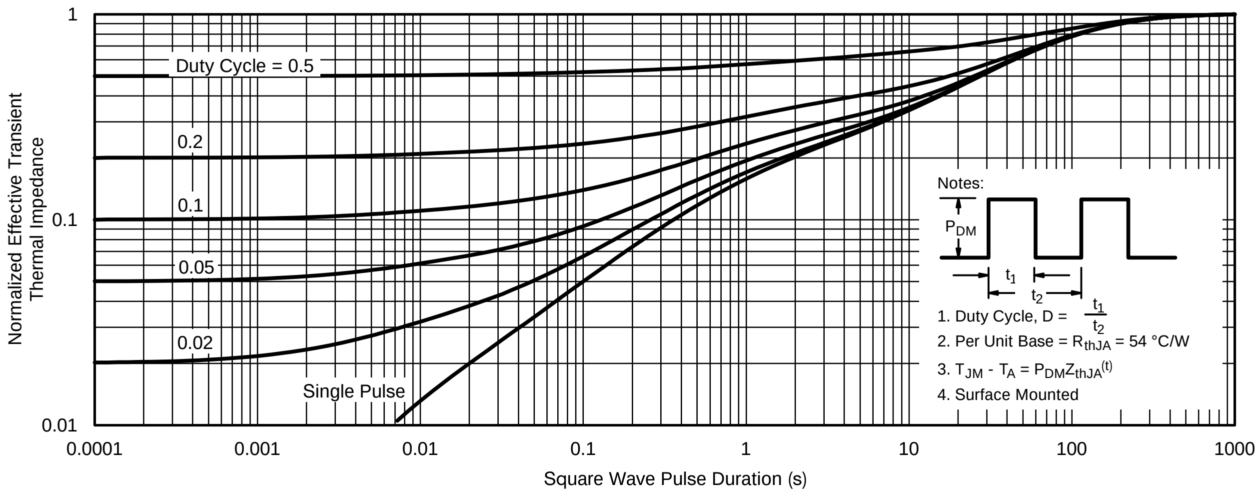
Power, Junction-to-Case



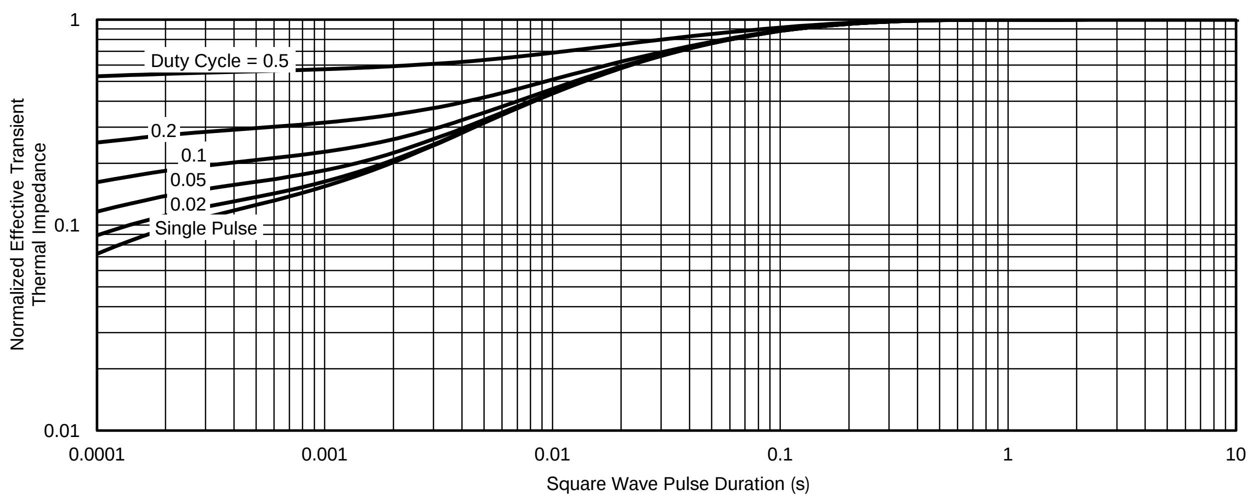
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J\,(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

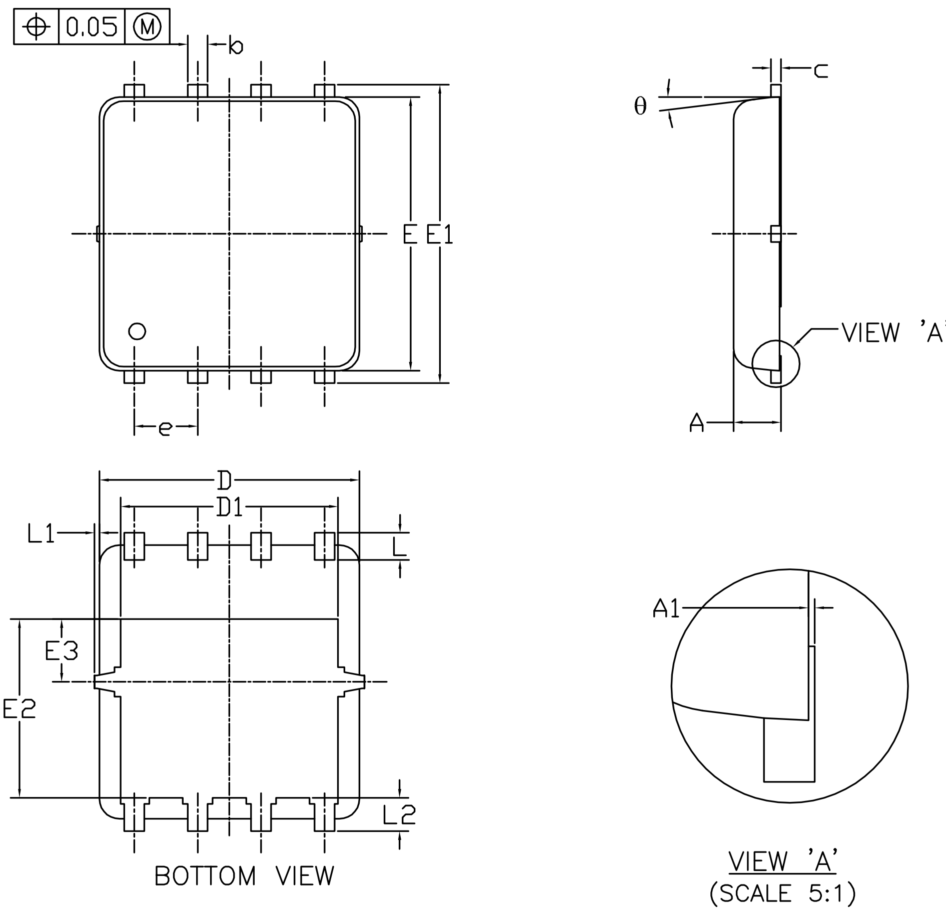


Normalized Thermal Transient Impedance, Junction-to-Ambient

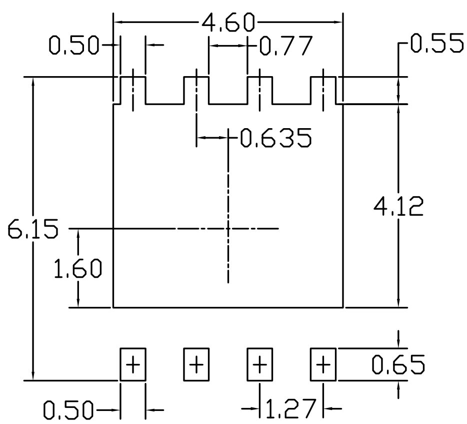


Normalized Thermal Transient Impedance, Junction-to-Case

DFN5x6_8L_EP1_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

UNIT: mm

NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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